KEEP THIS COPY FOR REPRODUCTION PURPOSES MASTER COPY

## REPORT DOCUMENTATION PAGE

Form Approved OMB No. 0704-0188

Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Warrier, to

1. AGENCY USE ONLY (Leave blank)

TITLE AND SUBTITLE

2. REPORT DATE

1990 Gordon Research Conference on Crystal Growth

3. REPORT TYPE AND DATES COVERED

April 1990

Final

3/1/90 <u>- 10/31/90</u>

5. FUNDING NUMBERS

DAAL03-90-G-0065

AUTHOR(S)

AD-A223

Margaret Brown

NG ORGANIZATION

Gordon Research Conferences, Inc Univ of Rhode Island Kingston, RI 02881

PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES)

SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES)

J. S. Army Research Office

P. O. Box 12211

Research Triangle Park, NC 27709-2211

10. SPONSORING / MONITORING AGENCY REPORT NUMBER

ARO 27332.1-EL-CF

11. SUPPLEMENTARY NOTES

The view, opinions and/or findings contained in this report are those of the author(s) and should not be construed as an official Department of the Army position, policy, or decision, unless so designated by other documentation.

12a. DISTRIBUTION / AVAILABILITY STATEMENT

12b. DISTRIBUTION CODE

Approved for public release; distribution unlimited.

13. ABSTRACT

The program was designed to present a range of topics and views within the broad theme of the conference. Sessions included papers on bulk and thin film crystal growth experiments and modeling, high T<sub>c</sub> superconductors (uses and crystal growth), II-VI compounds, and crystal characterization. Twenty full length papers were presented in eight sessions, chaired by acknowledged experts in the session field. Each session chair gave an introduction to his session and fostered discussions following the presentations. Two papers included impressive videotape displays of the theory and practice of crystal growth that greatly enhanced the understanding of the subjects verbally presented. The format of the Gordon conference allows ample unstructured time for informal discussion of program and other related topics, and participants remarked on how much they enjoyed these active discussion periods to pursue points brought up in the 'formal' sessions. Students and newcomers to the crystal growth community gained much from interacting informally with experienced scientists and learning from them. One session devoted to short verbal presentations of posters, to introduce authors and topics to the audience, proved to be a very successful experiment. Poster viewing sessions followed later, when authors were able to discuss their work in more detail.

14. SUBJECT TERMS

Conference, Crystal Growth, Superconductors, Thin Films

15. NUMBER OF PAGES

16. PRICE CODE

SECURITY CLASSIFICATION OF REPORT UNCLASSIFIED

SECURITY CLASSIFICATION OF THIS PAGE UNCLASSIFIED

19. SECURITY CLASSIFICATION OF ABSTRACT

20. LIMITATION OF ABSTRACT

UNCLASSIFIED

Standard Form 298 (Rev. 2-89)

Prescribed by ANSI Std. 239-18 298-102

UL.

10 4 S 14 108

NSN 7540-01-280-5500

## GORDON RESEARCH CONFERENCE ON CRYSTAL GROWTH

## Casa Sirena Marina Hotel, Oxnard, CA March 11-16 1990

## Chairman's Report for US Army Research Office

The Gordon Conference on Crystal Growth had as its theme: "Crystals for Electronic, Optical, and Superconducting Applications", to reflect topics of current and future interest in the field of crystal growth as perceived by the Chairman and Vice-Chairman of the 1990 conference. The conference attracted sixty five participants from industry (27), universities (20), national laboratories (7) and overseas (11). The mix of participants from experienced leaders in the field to university students benefitted all.

The program was designed to present a range of topics and views within the broad theme of the conference. Sessions included papers on bulk and thin film crystal growth experiments and modeling, high T<sub>c</sub> superconductors (uses and crystal growth), II-VI compounds, and crystal characterization. Twenty full length papers were presented in eight sessions, chaired by acknowledged experts in the session field. Each session chair gave an introduction to his session and fostered discussions following the presentations. Two papers included impressive videotape displays of the theory and practice of crystal growth that greatly enhanced the understanding of the subjects verbally presented. The format of the Gordon conference allows ample unstructured time for informal discussion of program and other related topics, and participants remarked on how much they enjoyed these active discussion periods to pursue points brought up in the 'formal' sessions. Students and newcomers to the crystal growth community gained much from interacting informally with experienced scientists and learning from them. One session devoted to short verbal presentations of posters, to introduce authors and topics to the audience, proved to be a very successful experiment. Poster viewing sessions followed later, when authors were able to discuss their work in more detail.

The program introduced many new aspects of crystal growth, including strained layer superlattices, quantum cluster growth, and vertical zone melting of GaAs. Modeling of growth processes has become very sophisticated now that powerful computers are available for solving complex equations, and models are now capable of useful application to experimental crystal growth for improvement of crystal quality. However, there is still much active discussion on the mathematical models used to predict crystal growth behavior. A very impressive paper was presented on dislocation generation in growing crystals, where dislocation distribution was successfully modeled. The characterization session presented a wide variety of techniques, including chemical etching for revealing dislocations, x-ray analysis for investigating thin film growth mechanisms, and electron microscopy for studying atomic-scale defect generation in crystals. The twenty one posters covered similar topics to those presented in the full paper sessions. The authors represented all sections of the crystal growth community, with five of the posters given by university students who are relatively new to the field. The poster session was of high caliber and included an excellent poster, and display of oxide crystals grown in Professor He Chong-Fan's Institute of Ceramics in Shanghai.

No proceedings are published to preserve the freedom of participants to voice their opinions, and present new and perhaps controversial data for review and frank discussion. The program, however, is available and is included here.

The site and organization of the conference were excellent, and conferees were very impressed with the high quality of the program and the high proportion of world renowned participants. It was an instructive, stimulating, interesting and enjoyable conference that we were very proud to be associated with. We are most grateful to USARO for granting funds that enabled us to invite the best speakers and participants, irrespective of their ability to finance themselves.

Margaret Brown (Conference Chairman)
Michael DiGiuseppe (Conference Vice-Chairman)

March 20 1990



Acces	Sluti For		
DTIC	CRA&I NOTIFICE Cation		
By			
Availability Codes			
Dist	Avail and/or Special		
A-1			

## GORDON RESEARCH CONFERENCES

## <u>CRYSTAL GROWTH</u> <u>CASA SIRENA MARINA HOTEL, OXNARD,CA</u>

MARGARET BROWN (Chairman)

MICHAEL A. DiGIUSEPPE (Vice Chairman)

MARCH 11-16, 1990

Sunday, March 11, Conference Opens

Afternoon: Arrival and Registration Check-in Early Evening: Informal Social (6 - 7 pm)

Evening: Dinner (7 pm)

Note: All Meals Included in Registration Cost: from Sunday March 11, Dinner, to Friday,

March 16, Lunch.

Monday, March 12 - Friday, March 16, Technical Sessions

THEME FOR THE CONFERENCE: Crystals for Electronic, Optical, and Superconducting

Applications

SESSION TITLE: Thin Film Growth: Experimental

Monday March 12 (AM)

Discussion Leader: D. W. Kisker

Speaker <u>Title of Presentation</u>

1. S. Irvine Energy Assisted Epitaxial Growth of II-VI Semiconductor

Thin Films

2. E. Bauser Semiconductor Liquid Phase Epitaxy: Growth and Properties

of Layers and Heterostructures

3. M. L. Steigerwald Growth of Quantum Clusters

SESSION TITLE: II-VI Compounds

Monday March 12, (PM)

Discussion Leader: A. L. Gentile

Speaker Title of Presentation

4. T. Taguchi Growth of Strained-Layer-Superlattices of Wide-Gap ZnS-

ZnSe and CdZnS-ZnS by Low Pressure OMCVD

5: J. Schulman Novel Properties and Applications of II-VI Superlattices and

Quantum Wells

SESSION TITLE: Short Verbal Presentation of Poster Papers Tuesday March 13, (AM)

Discussion Leader: R. A. Laudise

1, 2, 3. Posters (Approx. 20 total)

SESSION TITLE: Thin Film Growth / Interfaces: Modeling Tuesday March 13, (PM)

Discussion Leader: W. A. Tiller

Speaker Title of Presentation

4. F. Rosenberger Modeling of Growth Morphology with Anisotropic Surface

Kinetics

5. G. H. Gilmer Molecular Dynamics Studies of Heterointerfaces

SESSION TITLE: High T<sub>c</sub> Superconductors Wednesday March 14, (AM)

Discussion Leader: E.A. Giess

Speaker Title of Presentation

Properties and Processing of High T<sub>c</sub> Superconductors D.A. Cardwell 2. C. D. Brandle

The Growth of Oxide Crystals for Superconductor

R.S. Feigelson Growth of High T<sub>c</sub> Superconducting Fibers

SESSION TITLE: Crystals for Photonics Wednesday March 14, (PM)

Discussion Leader: P. Bordui

Speaker

R. H. Hopkins Crystals for Mid-infrared, Acousto-optic and Non-linear

Applications

D. Eimerl Crystal Growth and Properties of Non-linear Optical

Materials for Visible and Ultraviolet Applications

**SESSION TITLE:** Melt Growth: Modeling Thursday March 15, (AM)

Discussion Leader: D. T. J. Hurle

Title of Presentation Speaker

Melt Growth/Dendritic Fundamentals 1. M. E. Glicksman

A. A. Wheeler Analytical Modeling of Melt Growth Processes

J. Volkl Modeling Dislocation Generation in Czochralski Crystal

Growth of Semiconductors

SESSION TITLE: Melt Growth: Experimental Thursday March 15, (PM)

Discussion Leader: W. A. Bonner

Speaker Title of Presentation

4. K. Tada Growth and Characterization of InP single Crystals

R. Henry Vertical Zone Melting Growth of GaAs

**SESSION TITLE:** Characterization Friday March 16, (AM)

Discussion Leader: F. Szofran

Speaker Title of Presentation

1. K. Sangwal Chemical Etching: Principles and the Present Status P. H. Fuoss The Atomic Nature of Epitaxy: Using X-ray Analysis to

**Understand OMCVD Growth** 

H. P. Strunk Electron Microscopy of Semiconductors

#### SPECIAL ITEM:

Exhibition and Report of Recent Oxide Crystals Grown at the Shanghai Institute of Ceramics, China Given by Prof. He Chong-Fan

Friday March 16, Conference Ends After Lunch

NOTE: Papers 1hr. max. including generous question time.

#### POSTER PROGRAM

	POSTER PROGRAM .			
1	He Chong-Fan	Crystal Growth at Shanghai Institute of Ceramics, China, and Exhibition of Crystals. (S.I.C., China)		
2.	Derby / Brandon	Modeling of Effects of Internal Radiative Transport in Czochralski Crystal Growth. (U of Minnesota)		
3.	Colombo / Liao / Shaw	Application of Numerical Simulation on the Growth of (Hg,Cd) Te films by Liquid Phase		
4.	Maroudas / R.Brown	Epitaxy. (T.I.)  Modelling of Impurity and Dislocation  Dynamics in CZ Grown Si and LEC Grown  III-V Semiconductors. (MIT)		
5.	D-Hyun Kim / R.Brown	Modelling of Growth of II-VI Semiconductors by the Vertical Bridgman Method. (MIT)		
6.	Casagrande / M.Brown	The Growth by Vertical Bridgman and Characterization of Large Diameter CdTe		
7.	Andrews / Walck et al	Crystals. (Grumman) Microhardness Variations in II-VI Semi- conducting Compounds as a Function of		
8.	Szofran / Perry / Lehoczky	Composition. (UAH and MSFC, Huntsville) Automated Compositional Mapping of Narrow Band Gap Alloy Semiconductors. (MSFC, Huntsville)		
9.	Atherton	Characterization of Defects in LiCaAlF6:Cr.		
10.	Macrander / Lau	(L.L.N.L., Livermore) X-ray, Photoluminescence and Stoichiometry Mapping of In <sub>1-x</sub> Ga <sub>x</sub> As <sub>y</sub> P <sub>1-y</sub> . (AT&T Bell		
11.	Bordui / Bird et al	Labs, MH) Processing of Periodically-Poled Lithium Niobate for Nonlinear Optical Applications.		
12.	Morris	(Crystal Technology, Palo Alto) Crystal Growth of and Defects in Nonlinear Optical Oxide Crystals. (DuPont, Wilmington)		
13.	Logan / Tanbun-EK / Chu	Growth of Quantum Wells in the InGaAsP System by MOVPE. (AT&T Bell Labs, MH)		
14.	Cox	Vapor Levitation Epitaxy of Quantum Wires and Wire-like Structures Using Laterally		
15.	Bourret / Elliott	Propagating Surface Steps. (Bellcore, Red Bank) Growth of Semi-insulating and Doped GaAs single Crystals Using the VGF Technique.		
16.	Ramesh / Bonner et al	(Lawrence Berkeley Labs./ HP, San Jose) Engineering of Active and Passive Substrates for the Growth of High Temperature Super-		
17.	Greedan / Garrett et al	conductor Films. (Bellcore, and Rutgers U) The Growth and Characterization of Uranium Transition Metal Silicide Heavy Fermion Superconductors. (McMaster U, Hamilton;		
18.	Taborek	and AT&T Bell Labs) Growth and Characterization of Diamond Films. (U of CA at Irvine)		
19.	Banan	Directional Solidification of InGaSb Crystals (Clarkson U)		
20.	Parsons	Beta SiC Epitaxial Growth on TiC Substrates (Oregon Graduate Center)		
21.	Wei	Radiation Resistance and Fluorescence of Europium Doped BGO Crystals		

#### GORDON RESEARCH CONFERENCES

Crystal Growth March 12-16, 1990 Casa Sirena Resort Oxnard, California

## Registration List

Iwan Alexander University of Alabama Center for Microgravity & Mat's Re RI Building M-65 Huntsville, AL 35899	142 search	Edith Bourret Lawrence Berkeley Laboratory 1 Cyclotron Rd. MS 2-200 Berkeley, CA 94720	
Rosalia N. Andrews University of Alabama Dept. of Materials Sci. & Eng. 1150 lOth Avenue S	129	C. D. Brandle 20 Coppergate Dr. Basking Ridge, NJ 07920	138
Birmingham, AL 35294		Margaret Brown Grumman Corporation	259
L. Jeffrey Atherton Lawrence Livermore National Labora P.O. Box 5508	123 tory	2852 Kelvin Ave. Irvine, CA 92714	
L-490		David Cardwell	247
Livermore, CA 94550		Plessey Research Caswell Limited Allen Clark Research Centre	
Chan S. Bak	122	Caswell, Towcester Northants	
Hughes Research Labs. 3011 Malibu Canyon Rd.		NN12 8EQ United Kingdom	
Chemical Physics Dept., MS RL63 Malibu, CA 90263		Louis G. Casagrande Grumman CRC Mail Stop AO2-26	127
Moshen Banan	171	Bethpage, NY 11714-3580	
Clarkson University Dept. of Chemical Engineering	•	He Chong-Fan	127
Potsdam, NY 13699		Shanghai Institute of Ceramics 1295 Dingxi Road	127
Michael Banish	225	Shanghai P.R. 200050 China	
University of Alabama in Huntsvill		Ted Ciszek	153
Center for Microgravity & Mat's Re RI Building M-65 Huntsville, AL 35899	s.	Solar Energy Research Institute 1617 Cole Blvd., 1613 Golden, CO 80401	133
Elizabeth Bauser	131		
Max-Planck-Institut F. Festkoperfo	rschu	Herbert M. Cox	174
Heisenbergstr.l Stuttgart 80 D-7000 West Germany	,	Bellcore 331 Newman Springs Rd. RM 3X203	
W. A. Bonner Bellcore	134	Red Bank, NJ 07701-7040	
331 Newman Springs Rd.		Jeffrey J. Derby	
Room 3G-111		University of Minnesota	
Red Bank, NJ 07701		Dept. of Chemical Eng. & Mat. Sciol 151 Amundson Hall	ence
Peter Bordui Crystal Technology 1051 E. Meadow Circle	175	Minneapolis, MN 55455	

Palo Alto, CA 94303

## Crystal Growth Registration List - Page 2

		- <b>,</b> -	
Jim De Yoreo Lawrence Livermore Labs. L-250 Livermore, CA 94550	123	G. H. Gilmer AT&T BEll Laboratories Room 1D-447 600 Mountain Ave. Murray Hill, NJ 07914	136
M. A. DiGuiseppe AT&T Bell labs Room 7B 428 600Mountain Ave. Murray Hill, NJ 07974-2070 D. Eimerl	128	Martin E. Glicksman Rensselaer Polytechnic Inst. 110 8th Street Materials Engineering Dept. Troy, NY 12180-3590	253
LLNL L-490, P.O. Box 5508 Livermore, CA 04550		Lucinda Glicksman (guest of Martin E. Glicksman)	253
Robert Feigelson Stanford University Center for Materials Research Stanford, CA 94305-4045	102	R. Henry Naval Research Laboratory Code 6822 Overlook Ave. Washington, DC 20375-5000	176
Vicki feigelson (guest of Robert Feigelson) P. H. Fuoss	102	R. H. Hopkins Westinghouse Science/Tech. Center 1310 Buelah Rd. Pittsburgh, PA 15235	101
AT&T Bell Labs 4C 316 Crawfords Corner Rd. Holmdel, NJ 07733		T. J. Hurle RSRE St. Andrew's Rd. Malvern Wores WR14 3PS UK	156
Jim Garrett McMaster University I.M.R., ABB 439 1280 Main St., West Hamilton, Ont., L8S 4Ml, CANAD	203 A	S. J. C Irvine RSRE St. Andrews Rd. Malvern Worcester, WR14 3PS UK	
Holly Garrett (guest of Jim Garrett)	203	Vassilis G. Keramidas Bellcore 331 Newman Springs Rd.	159
Ricky Steven (guest of Jim Garrett)	201	3Z 375 Red Bank, NJ 07701	
Tamon Steven (guest of Jim Garrett)	201	Do H. Kim MIT 77 Massachusetts Ave., Room 66-36	124 57
A. Gentile Hughes Research Labs. 3011 Malibu Canyon Rd.	154	Dept. of Chemical Engineering Cambridge, MA 02139	
Bldg. 250 RL62 Malibu, CA 90265 Eeward A. Geiss	244	Hiroshi Kimura Hughes Research Laboratory 3011 Malibu Canyon Rd. RL 63	266
IBM Research Division Dept. 431	2473	Malibu, CA 90265	
Box 218 Yorktown Heights, NY 10598		D.W. Kisker AT&T BEll Labs Crawfords Corner Rd., Room 4G632 Holmdel, NJ 07733	162

# Crystal Growth Registration List - Page 3

Registration List - Page 3			
R. A. Laudise AT&T Bell Laboratories Room 1A-264 300 Mountain Ave. Murray Hill, NJ 07974		Thomas A.Nyce University of Alabama Center for Microgravity and mat's RI Building M-65, UAH Huntsville, AL 35899	225 Res.
Pok-Kai Liao Texas Instruments P.O. Box 655936, M/S 154 Dallas, TX 75265	173	Jim Parsons OGI, Dept.of AP & EE 19600 N. W. Van Neumann Drive Beaverton, OR 97006-1990	172
Ralph A. Logan AT&T BEll Labs Room 4-228 Murray Hill, NJ 07914	234	Michael W. Price University of Alabama at Birmingha Dept. of materials Science & Engin 1150 10th Ave., South Birmingham, AL 35294	122 am neering
Albert Macrander AT&T BEll Labs Room 7F-318 600 Mountain Ave. Murray Hill, NJ 07974	202	Franz Rosenberger University of Alabama, Huntsville CMMR/M-67 Huntsville, AL 35899	142
Dimitrios Marcudas MIT 77 Massaxhusetts Ave., Room 66-256 Dept. of Chemical Engineering Cambridge, MA 02139	124	Keshra Sangwal Inst. de Ciencia de Materials CSI Marti L Granques S/N Barcelona 08028, Spain	224 C
Anthony Matusko 4210 Elizabeth Lane Annandale, NJ 22003		J. Schulman Off- Hughes Research labs., RL62 3011 malibu Canyon Rd. Malibu, CA 90265	Site
Greg Mihalik EG&G Energy Measurements, Inc. 130 Robin Hill Road Material Sciences Department Goleta, CA 93117	149	Carlos Schezov Dep. of Metals & Materials - UBC 6350 Stores Rd. Vancouver, BC V6T 1W5 Canada	229
Roch R. Monchamp EG&G Energy Measurements, Inc. 130 Robin Hill Rd. Material Sciences Department Goleta, CA 93117	222	Paul J. Schlicta Crystal Research 1441 Synnyside Terrace San Pedro, CA 90732	135
Patricia A. Morris E. I. Dupont de Nemours & Co. Central Research & Development Experimental Station E306/6A Wilmington, DE 19880-0306	223	M. L. Steigerwald AT&T Bell Laboratories ID-345 600 Mountain ave. Murray Hill, NJ 07974 H. P.Strunk	125 401
A. D. Morrison Jet Propulsion Lab. 4800 Oak Grove Drive 183-801 Pasadena, CA 91109	205	Universitat Erlangen-Nurnberg Inst. fur Werkstoffwissenschaften Haberstr.2 Erlangen, 8520 West Germany	- <del>-</del>

205

Sandra Morrison (guest of A. D. Morrison)

## Crystal Growth Registration List - Page 4

Regi	strat
Ching-Hua Su Universities Space Research Associa ES75 NASA/Marshall Space Flight Center	204 tion
Huntsville, AL 35812	
F. R. Szofran ES75 NASA Marshall Space Flight Center Huntsville, AL 35812	133
Peter Taborek University of California, Irvine Physics Dept. Irvine, CA 92717	
K. Tada Sumimoto Electric Industries, Ltd. 1-1-3 Shimaya, Konohana-Ku Osaka 554 Japan	228
Tsunemasa Taguchi Osaka University 2-1 Yamaka-Oka Suita, Osaka 565 Japan	230
W. A. Tiller Stanford University Department of Materials Science & E Stanford, CA 94305-2205	243 ing.
Jean Tiller (guest of W. A. Tiller)	243
Lodewijk Van Den Berg EG&G/EM Santa Barbara Operationa 130 Robin Hill Road Goleta, CA 93117	231
Johannes Volkl Siemens AG ZFE ME(AMF)33, G Scharowsky-Str.2 Erlangen, D-8520 West Germany	133
Zhongying Wei California Inst. of Technology HEP 256-48, Caltech Lauristen lab. of High Energy Physi Pasadena, CA 91125	135 .cs

A. A. Wheeler Bristol University School of Maths University Walk Bristol, UK B58 lTW